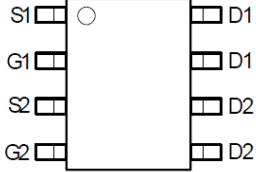
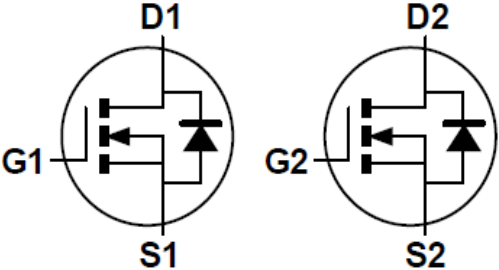


N-channel 60V, 20mΩ max.,8A
 SGT MOSFET S2 in SOP-8

Datasheet - Production data

1. Descriptions

SOP-8	Top View
	
Schematic Diagram	
	

Key Performance Parameters

Parameters	Value	Unit
BV_{DSS}	60	V
$R_{DS(on),max}$	20	mΩ
P_D	5.5	W
I_D	8	A

Features

- High Speed Power Switching, Logic Level
- Low Input Capacitance
- Low On-Resistance
- 100% UIS Tested
- Lead Free, Halogen Free
- Qualified for Automotive applications according to AEC-Q101.

Applications

- DC/DC Converter
- PD Charger
- Motor Driver
- Switching Voltage Regulator
- Power Management Functions

Type/Ordering Code	Package	Marking	Related Links
CSK200N06S2A	SOP-8	200N06S2A	See Appendix A

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2. Maximum Ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Absolute Maximum Ratings

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
V_{DS}	Drain-source voltage	-	-	60	V	$V_{GS}=0V$, $I_D=250\mu A$
V_{GS}	Gate source voltage	-20	-	20	V	static; AC ($f>1\text{ Hz}$)
I_D	Continuous drain current	-	-	8	A	$T_C=25^\circ\text{C}$
$I_{D,pulse}$	Pulsed drain current	-	-	40	A	$T_C=25^\circ\text{C}$
P_D	Power dissipation	-	-	5.5	W	$T_C=25^\circ\text{C}$
E_{AS}	Avalanche energy, single pulse ¹⁾	-	-	81	mJ	$I_D=18A$; $V_{DD}=50V$
T_j, T_{stg}	Operating and storage temperature	-55	-	175	$^\circ\text{C}$	-

3. Thermal Characteristics

Thermal Characteristics

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		
R_{thJC}	Thermal resistance, junction – Case	-	-	27	$^\circ\text{C/W}$	$T_C = 25^\circ\text{C}$
R_{thJA}	Thermal resistance, junction - ambient ²⁾	-	-	70	$^\circ\text{C/W}$	$T_C = 25^\circ\text{C}$

4. Electrical Characteristics

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Symbol	Parameter	Values			Unit	Test Condition
		Min.	Typ.	Max.		

Off Characteristics

$V_{(BR)DSS}$	Drain-source breakdown voltage	60	-	-	V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Zero gate voltage drain current	-	-	1	μA	$V_{DS}=60V, V_{GS}=0V$
I_{GSS}	Gate-source leakage current	-	-	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$

On Characteristics³⁾

$V_{(GS)th}$	Gate threshold voltage	1.0	-	3.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$R_{DS(on)}$	Drain-source on-state resistance	-	16	20	m Ω	$V_{GS}=10V, I_D=20A$
R_G	Gate resistance	-	1.8	-	Ω	$V_{DD}=0V, V_{GS}=0V, F=1MHz$
g_{fs}	Transconductance		30		S	$V_{DS}=5V, I_D=20A$

Dynamic Characteristics

C_{iss}	Input capacitance	-	653	-	pF	$V_{GS}=0V, V_{DS}=30V,$ $F=250KHz$
C_{oss}	Output capacitance	-	110	-	pF	
C_{rss}	Reverse transfer capacitance	-	5.3	-	pF	

Switching Characteristics⁴⁾

$t_{d(on)}$	Turn-on delay time	-	13	-	ns	$V_{DD}=30V, V_{GS}=10V,$ $I_D=20A, R_G=10\Omega$
t_r	Turn-on rise time	-	25	-	ns	
$t_{d(off)}$	Turn-off delay time	-	26	-	ns	
t_f	Turn-off fall time	-	10	-	ns	
Q_g	Gate charge total	-	12.4	-	nC	$V_{DD}=30V, I_D=20A, V_{GS}=0 \text{ to } 10V$
Q_{gs}	Gate to source charge	-	1.5	-	nC	
Q_{gd}	Gate to drain charge	-	2.5	-	nC	

Reverse Diode Characteristics

V_{SD}	Diode forward voltage ³⁾	-	0.9	1.2	V	$V_{GS}=0V, I_F=20A$
I_S	Diode forward current ²⁾	-	-	2.5	A	
t_{rr}	Reverse recovery time	-	38	-	ns	$V_{GS}=0V, I_F=20A,$ $di_F/dt=100A/\mu s^3)$
Q_{rr}	Reverse recovery charge	-	17	-	μC	

1) $V_{DD}=50V, L=0.5mH, R_G=25\Omega$, Starting $T_j=25^\circ\text{C}$.

2) Surface Mounted on FR4 Board, $t \leq 10 \text{ sec}$.

3) Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

4) Guaranteed by design, not subject to production

5. Electrical Characteristics Diagrams

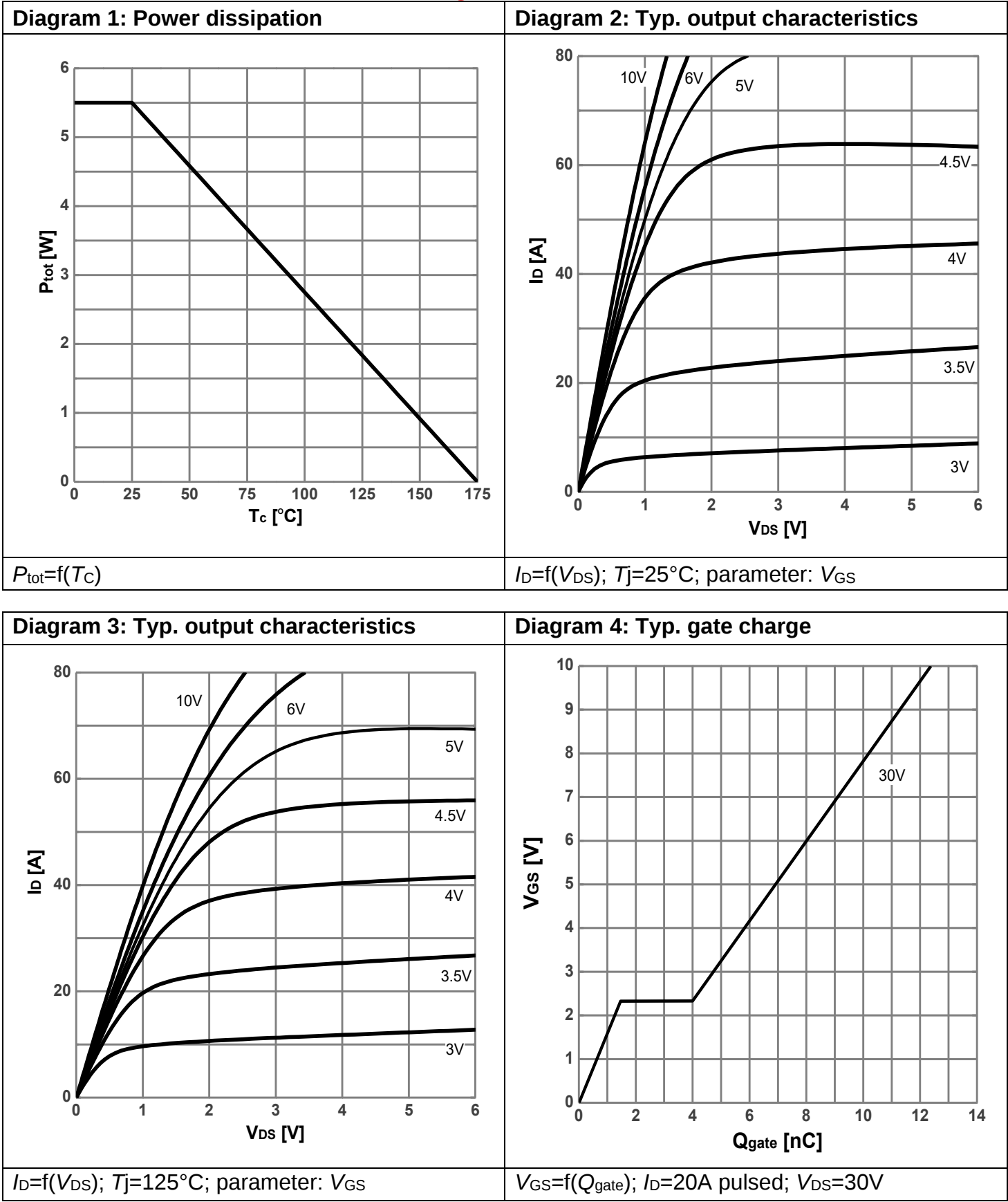
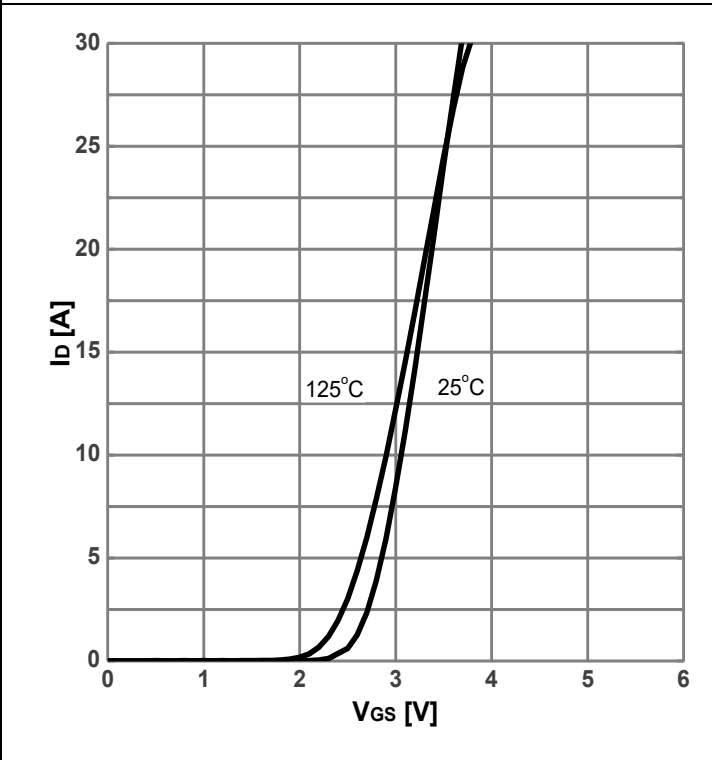
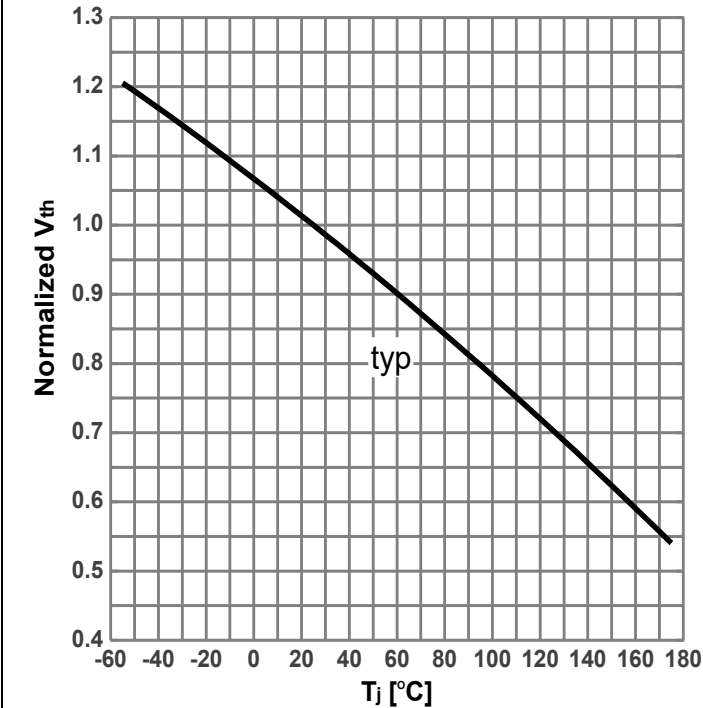


Diagram 5: Typ. transfer characteristics



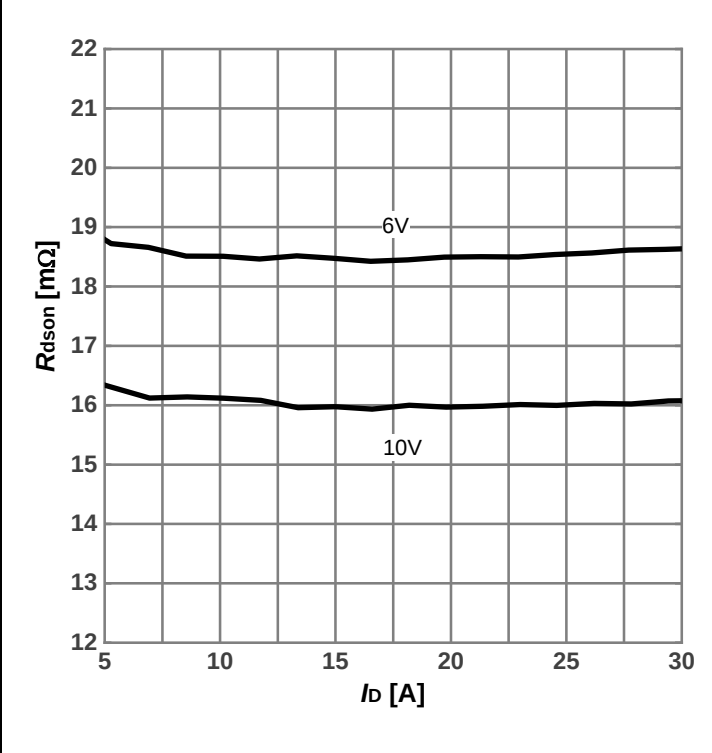
$I_D=f(V_{GS})$; $V_{DS}=5V$; parameter: T_j

Diagram 6: Gate threshold voltage vs. Junction temperature



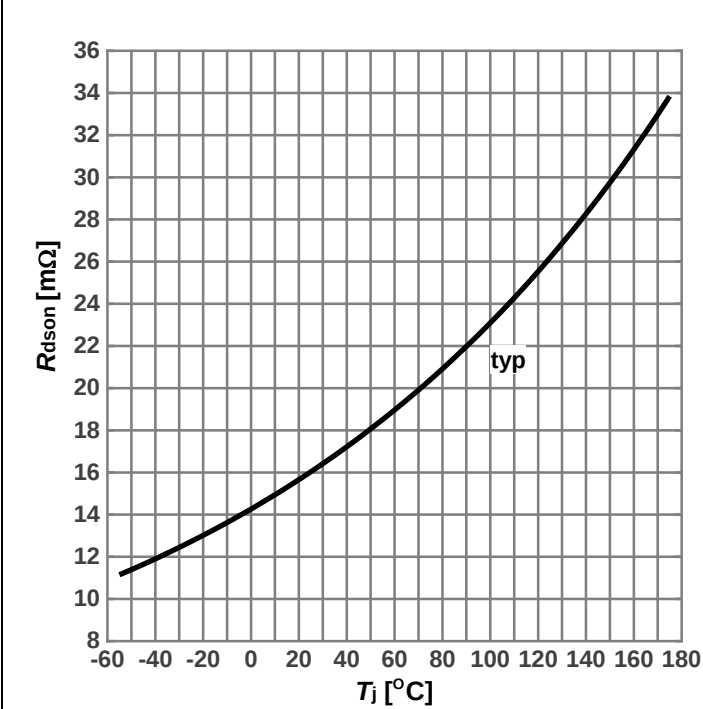
$V_{th}=f(T_j)$; $I_D=250\mu\text{A}$

Diagram 7: On-state resistance vs. Drain current



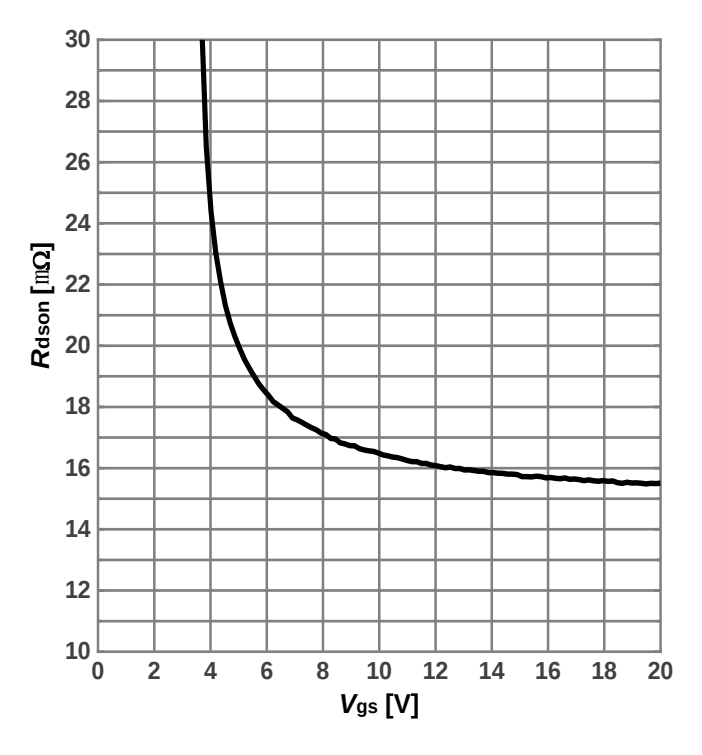
$R_{DS(on)}=f(I_D)$; $T_j=25^{\circ}\text{C}$; parameter: V_{GS}

Diagram 8: On-state resistance vs. Junction temperature



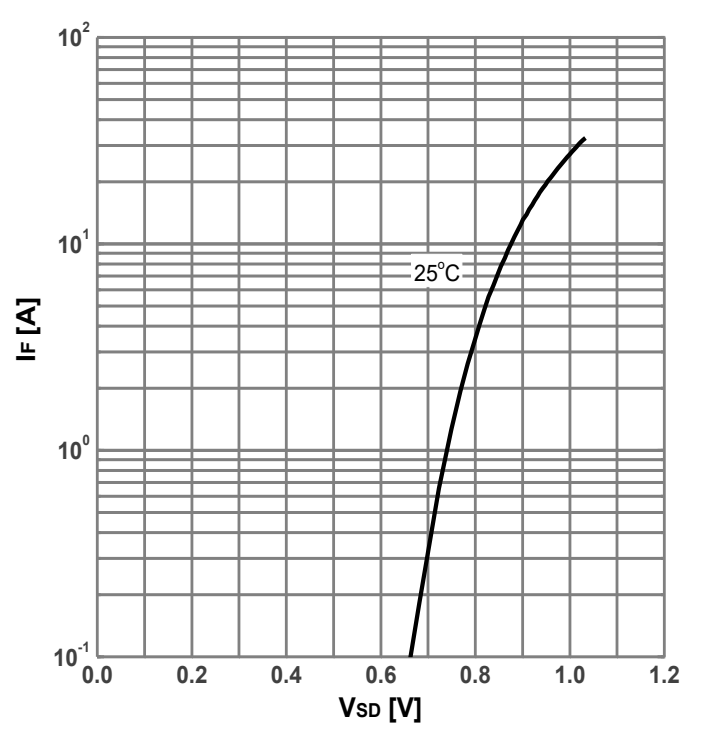
$R_{DS(on)}=f(T_j)$; $I_D=20A$; $V_{GS}=10V$

Diagram 9: On-state resistance vs. Vgs characteristics



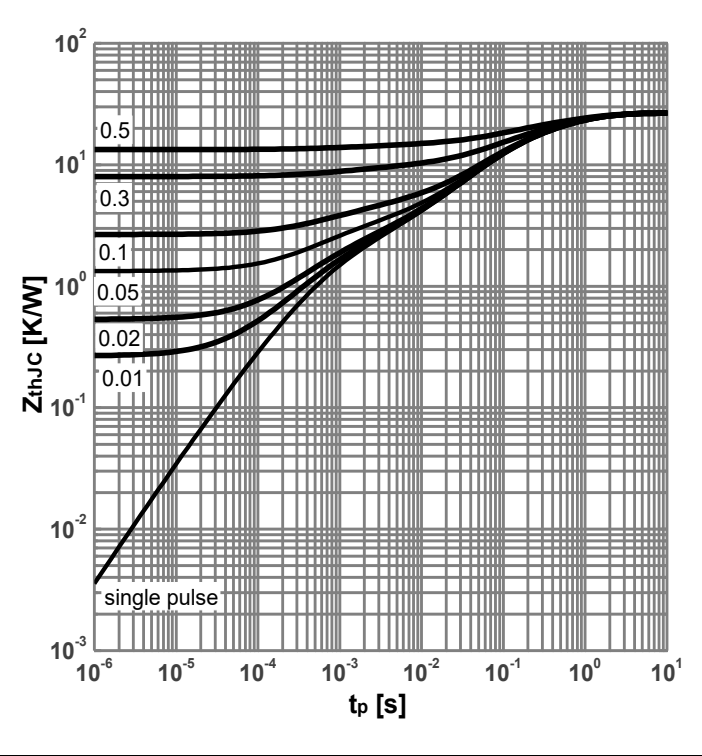
$R_{DS(on)}=f(V_{gs}); T_j=25^{\circ}C; I_D=20A$

Diagram 10: Forward characteristics of reverse diode



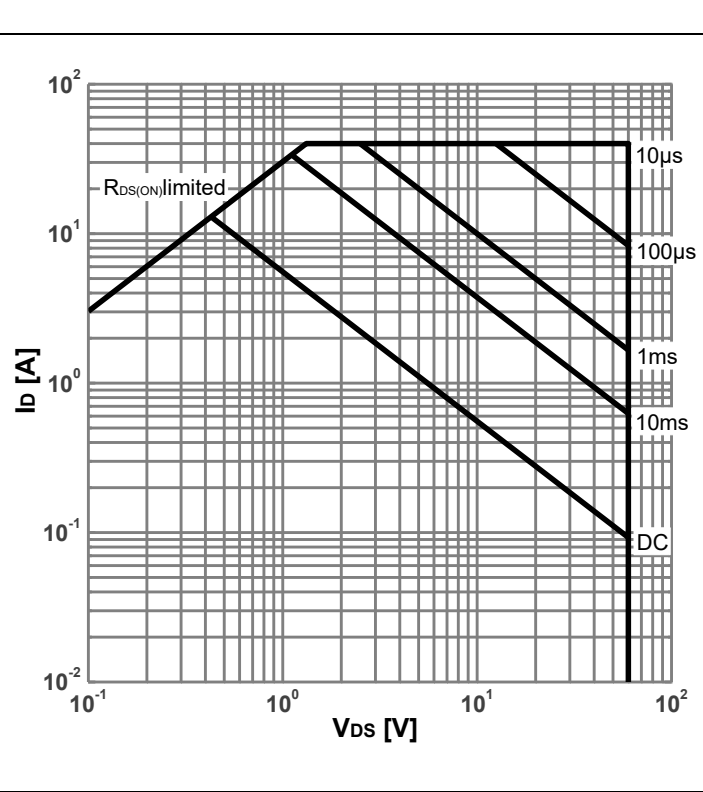
$I_F=f(V_{SD}); \text{parameter: } T_j$

Diagram 11: Max. transient thermal impedance

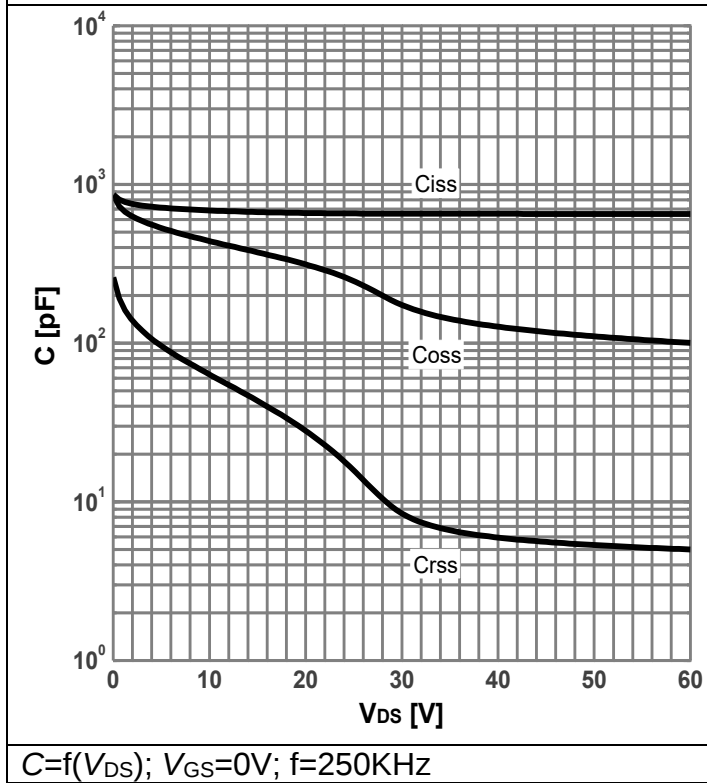


$Z_{thJC}=f(t_p); \text{parameter: } D= t_p/T$

Diagram 12: Safe operating area



$I_D=f(V_{DS}); T_j=25^{\circ}C; D=0; \text{parameter: } t_p$

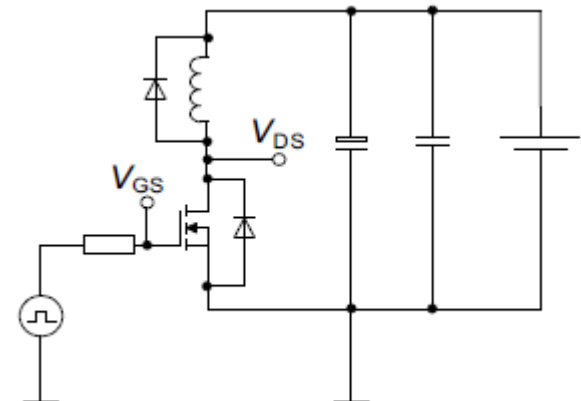
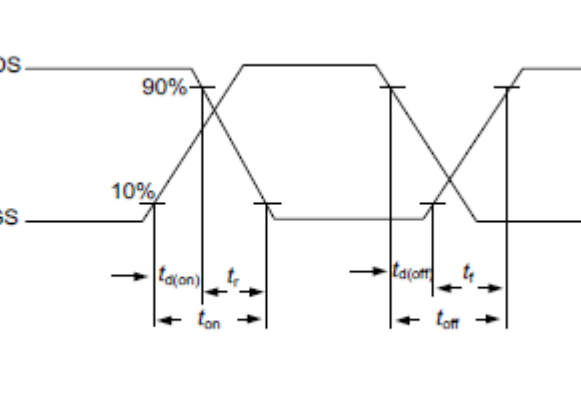
Diagram 13: Typ. capacitances

6. Test Circuits

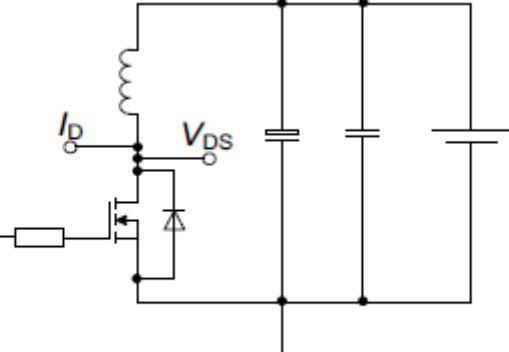
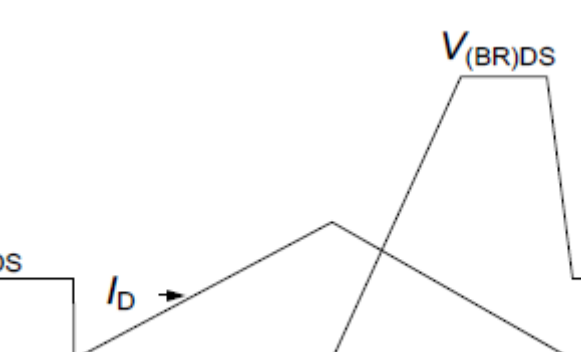
Diode Characteristics

Test circuit for diode characteristics $R_{g1} = R_{g2}$	Diode recovery waveform $V_{DS(peak)}$ V_{DS} I_F t_F t_T t_S dI_F/dt Q_F Q_S $10\% I_{rm}$ I_{rm} dI_T/dt $t_{rr} = t_F + t_S$ $Q_{Tr} = Q_F + Q_S$
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Switching Times

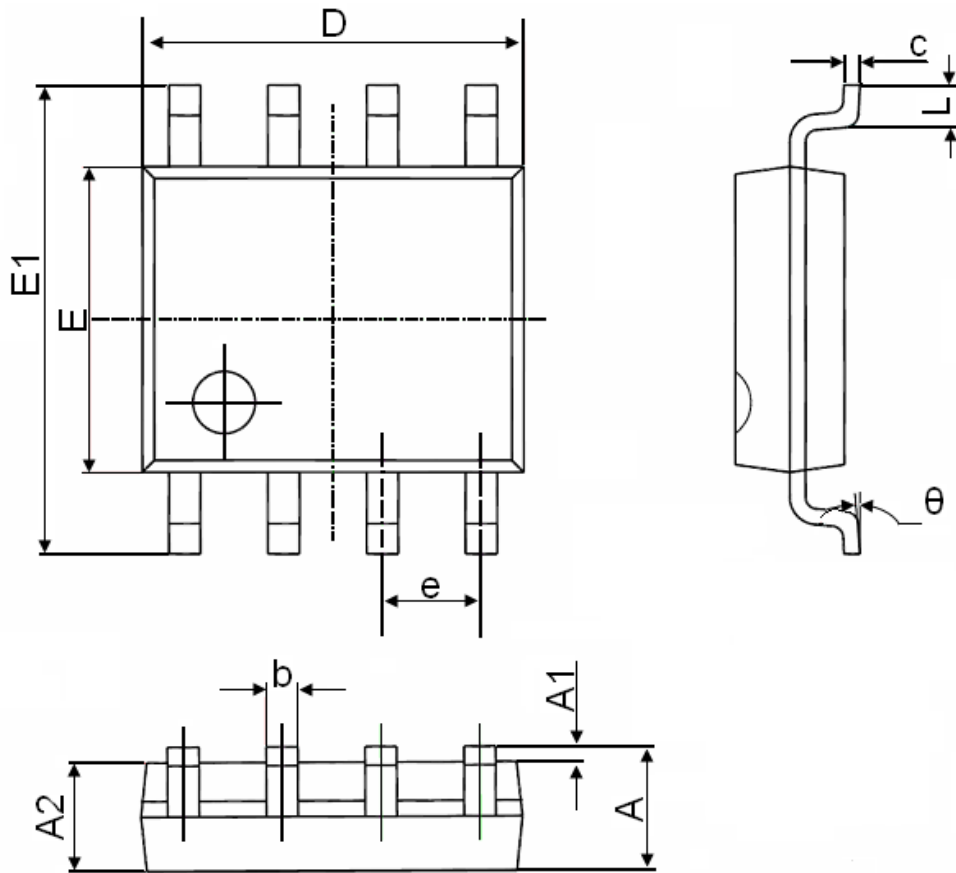
Switching times test circuit for inductive load	Switching times waveform
	

Unclamped Inductive Load

Unclamped inductive load test circuit	Unclamped inductive waveform
	

7. Package Outlines

Figure 1 Outline SOP-8 Dimensions in mm



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

8. Appendix

CoolSemi Webpage: www.coolsemi.com.